

2301

1.5 Watt - 20 Volts, Class C Microwave 2300 MHz

The 230 Class C, ballastin transisto	ERAL DESCRIPTION 1 is a COMMON BASE transistor cap 5 RF output power at 2300 MHz. Gold 1 are used to provide high reliability a 1 or uses a fully hermetic High Temperat	I metalization and diffused and supreme ruggedness. The sure Solder Sealed package.	CASE OUTLINE 55 BT- Style 1
ABSC	OLUTE MAXIMUM RATI	NGS	
Maximu	m Power Dissipation @ 25°C	5.6 Watts	
Maxim BVces	um Voltage and Current Collector to Emitter Voltage	45 Volts	
BVebo	Emitter to Base Voltage	3.5 Volts	
Ic	Collector Current	0.3 A	
Maxim	um Temperatures		
	Tamananatura	$-65 \text{ to } + 200^{\circ}\text{C}$	
Storage	remperature	-0.010 ± 200 C	

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η _c VSWR ₁	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 2.3 GHz Vcb = 20 Volts Po = 1.5 Watts As Above F = 2.3 GHz, Po = 1.5 W	1.5 8.0	40	0.24 30:1	Watt Watt dB %

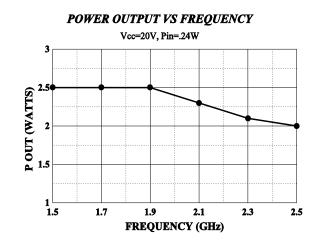
BVces BVebo h _{FE}	Collector to Emitter Breakdown Emitter to Base Breakdown Current Gain	Ic = 10 mA Ie = 1.0 mA Vce = 5 V, Ic = 100 mA	45 3.5 10			Volts Volts
Cob θjc	Output Capacitance Thermal Resistance	F = 1.0 MHz, Vcb = 22V	10	4.0	31	pF °C/W

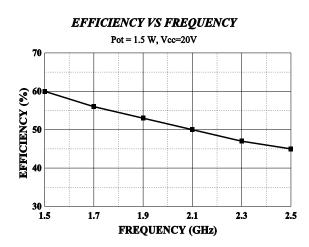
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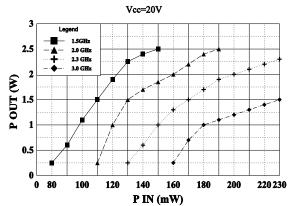
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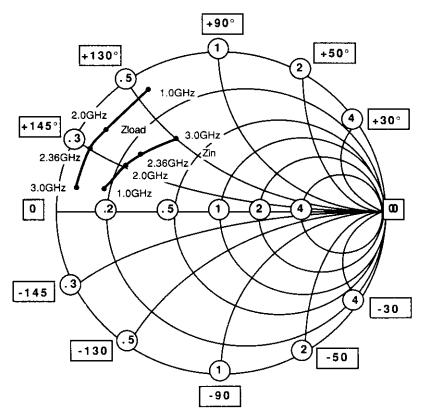
TRANSFER CHARACTERISTICS VS FREQUENCY



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NORMALIZED IMPEDANCE AND ADMITTANCE COORDINATES



NORMALIZED TO A 50 OHM SYSTEM.

FREQUENCY	R	in +JX	FREQUENCY	RZIG	bad +JX
1000	8.5	7.5	1000	5	22
2000	11	15	2000	4	17
2300	13	18	2300	3.7	14
3000	16	2 0	3000	2.8	6.5